Abstract of the Disclosure

The present invention provides a ferroelectric memory device capable of suppressing a defect generation due to a charge impact and a method for fabricating the same. The ferroelectric memory device includes: a semiconductor substrate on which a transistor is formed; a semiconductor substrate structure having a transistor; a lower electrode formed on an interfacial insulation layer and connected to a source/drain region of the transistor; an isolating insulation layer on the interfacial insulation layer; a ferroelectric layer covering the isolating insulation layer and lower electrode; an oxygen vacancy compensation layer being formed on the ferroelectric layer and compensating an oxygen vacancy caused by deoxidization of a composition of the ferroelectric layer; and an upper electrode formed on the oxygen vacancy compensation layer.